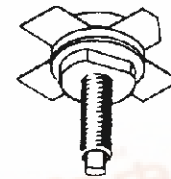




SD1455

RF & MICROWAVE TRANSISTORS TV/LINEAR APPLICATIONS

- 170 - 230 MHz
- 25 VOLTS
- IMD – 55dB
- COMMON EMITTER
- GOLD METALLIZATION
- HIGH SATURATED POWER CAPABILITY
- DIFFUSED EMITTER BALLAST RESISTORS
- DESIGNED FOR HIGH POWER LINEAR OPERATION
- $P_{OUT} = 20 \text{ W MIN. WITH } 8.0 \text{ dB GAIN}$

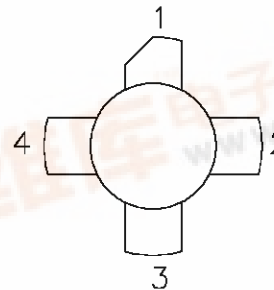


.500 4L STUD (M130)
epoxy sealed

ORDER CODE
SD1455

BRANDING
SD1455

PIN CONNECTION



- | | |
|--------------|------------|
| 1. Collector | 3. Base |
| 2. Emitter | 4. Emitter |

DESCRIPTION

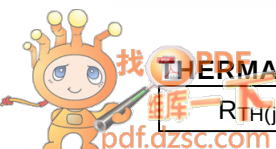
The SD1455 is a gold metallized epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for high linearity Class A operation in VHF and Band III television transmitters and transposers.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	35	V
V_{CES}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Device Current	8.0	A
P_{DISS}	Power Dissipation	140	W
T_J	Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	– 65 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{\theta(j-c)}$	Junction-Case Thermal Resistance	1.5	$^{\circ}\text{C/W}$
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SD1455

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 50 mA	I _E = 0 mA	65	—	—	V
BV _{CER}	I _C = 50 mA	R _{BE} = 10 Ω	60	—	—	V
BV _{CEO}	I _C = 50 mA	I _B = 0 mA	35	—	—	V
BV _{EBO}	I _E = 10 mA	I _C = 0 mA	4.0	—	—	V
I _{CES}	V _{CE} = 50 V	V _{BE} = 0 V	—	—	5	mA
h _{FE}	V _{CE} = 5 V	I _C = 1 A	20	—	120	—

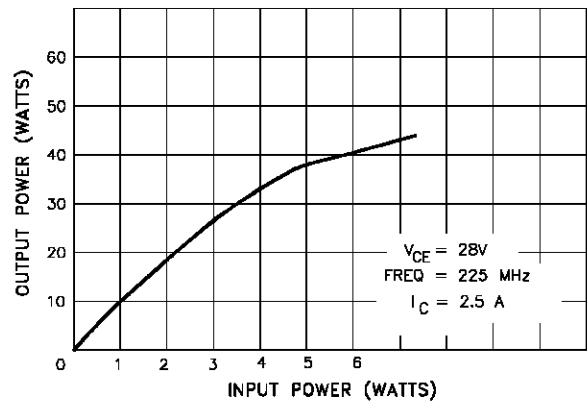
DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 225 MHz	V _{CE} = 25 V	I _C = 2.5 A	20	—	—	W
G _P	f = 225 MHz	V _{CE} = 25 V	I _C = 2.5 A	8.0	9.0	—	dB
IMD ₃ *	P _{OUT} = 14 W	V _{CE} = 25 V	I _C = 2.5 A	—	−55	—	dBc
C _{OB}	f = 1 MHz	V _{CB} = 30 V		—	—	85	pF

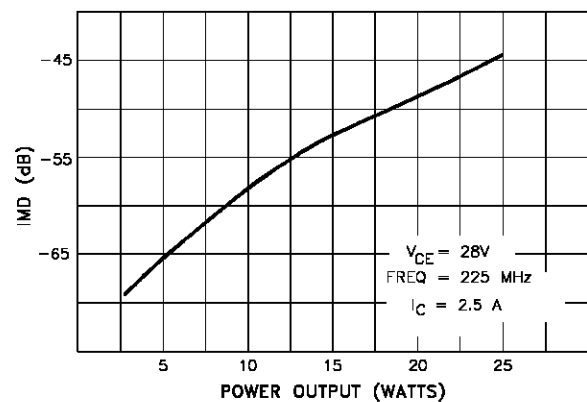
Note: * f = 225 MHz
 3 Tone Testing
 Vision Carrier −8dB/ref
 Sound Carrier −7dB/ref
 Sideband Carrier −16dB/ref

TYPICAL PERFORMANCE

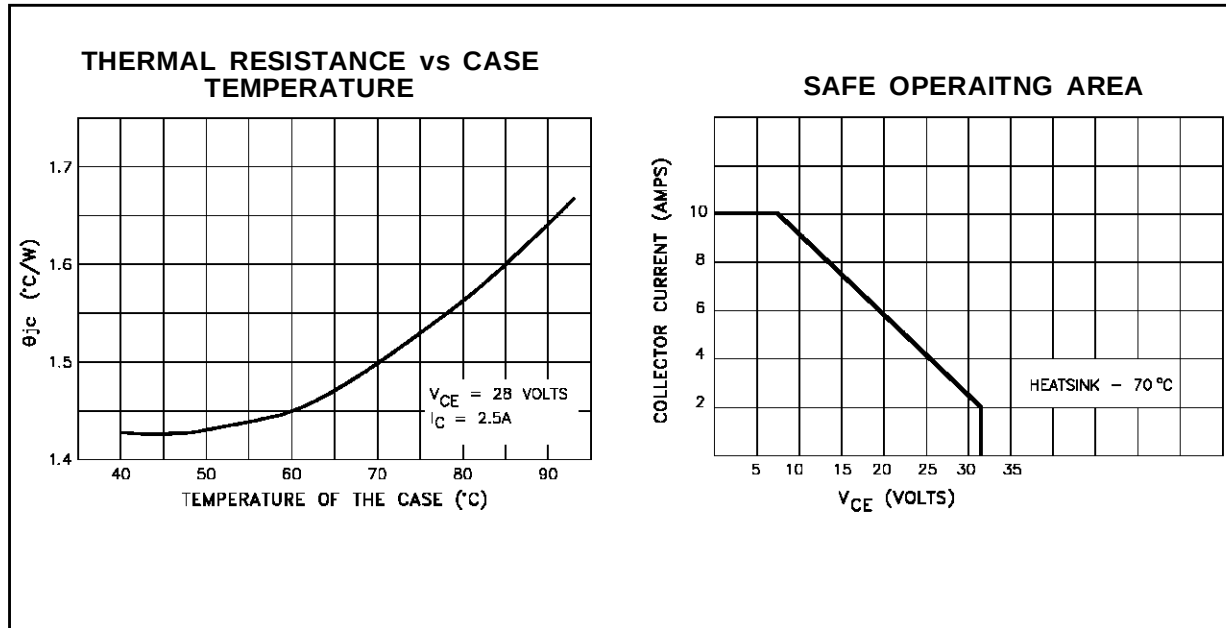
POWER OUTPUT vs POWER INPUT



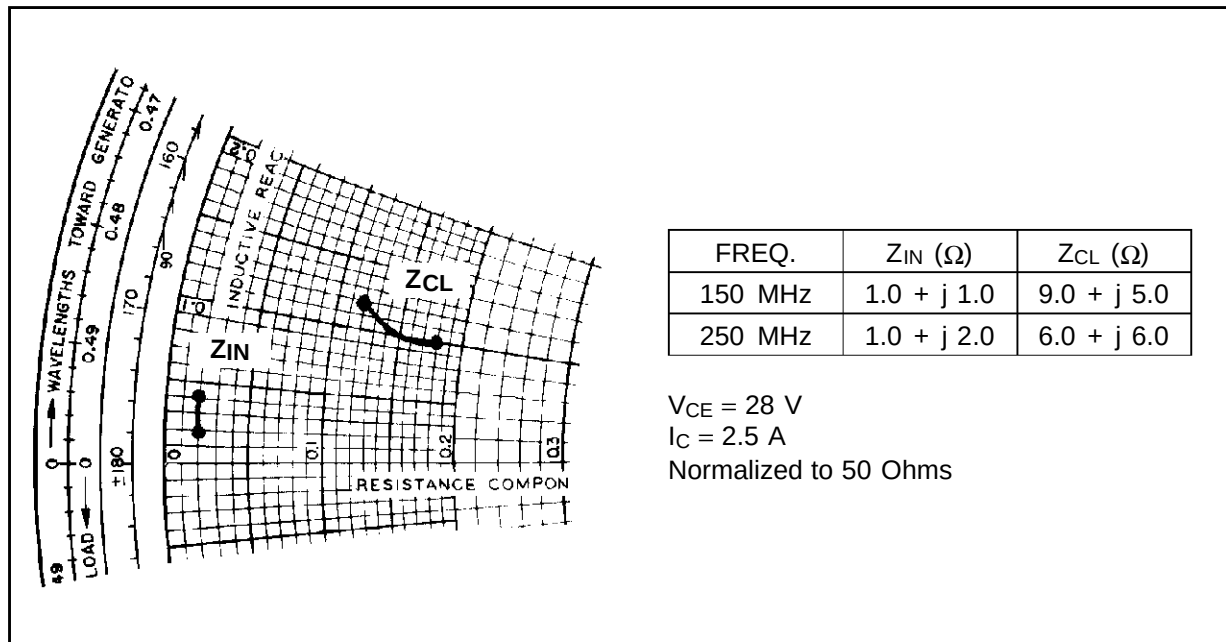
INTERMODULATION DISTORTION vs POWER OUTPUT



TYPICAL PERFORMANCE (CONT'D)



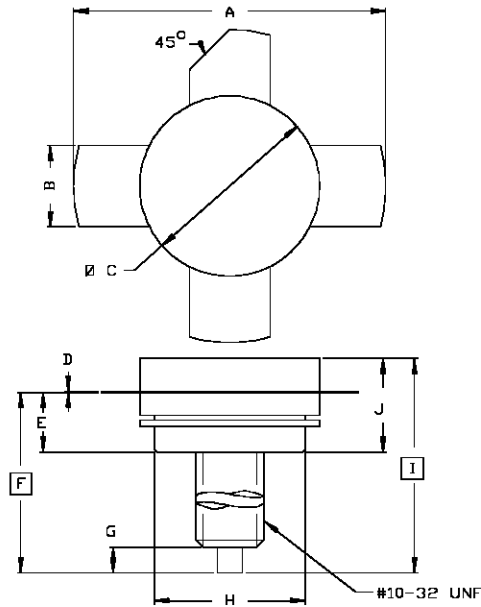
IMPEDANCE DATA



SD1455

PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0130



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25,65	1.050/26,67
B	.220/5,59	.230/5,84
C	.495/12,57	.505/12,83
D	.003/0,08	.007/0,18
E	.160/4,06	.180/4,57
F	.622/15,80	
G	.100/2,54	.130/3,31
H	.415/10,54	.425/10,80
I	.720/18,29	
J	.250/6,35	.290/7,37

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